METHOD FOR ELIMINATING BRIDGING DEFECT IN VIA FIRST DUAL DAMASCENE PROCESS

Abstract of Disclosure

A via-first dual damascene process is disclosed. When forming trench lines directly above two small pitched, dense via openings having diameter that is substantially equal to the line width of the trench lines, the trench photoresist is biased on the via openings to partially mask the sidewalls of the two dense via openings. By doing this, via-to-via bridging defects can be avoided.

Figure 13